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ONERA

THE FRENCH AEROSPACE LAB



# MUSCA SEP3 / TERRIFIC

*The SEE prediction software platform by ONERA*

COMET

December 13<sup>th</sup> 2022

# Talk overview

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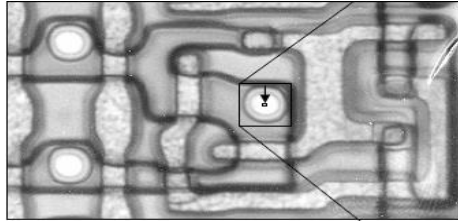
- **Context of the SEE prediction**
- **Global simulation framework of SEE modeling at ONERA**
  - Tools methodology
  - Inputs overview
  - Physical modeling
- **Example of SEE modeling at ONERA: from emerging effects to hardening by design support**
  - From emerging effects
  - To hardening by design support

# Context for SEE prediction

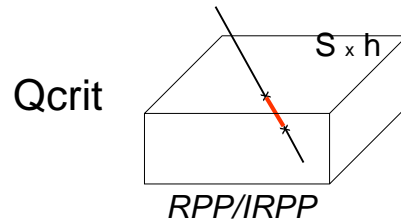
- The evolution of SEE prediction methodologies depends on:  
→ **Scaling, architecture, materials**

CMOS

1980 :  $1700 \mu\text{m}^2$



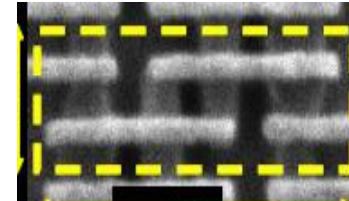
Basic Approach



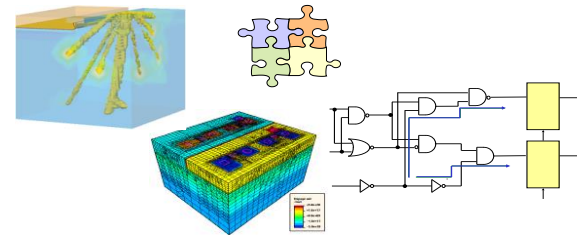
~Scell / 70000

Today: 5nm ~  $0.025/0.021 \mu\text{m}^2$

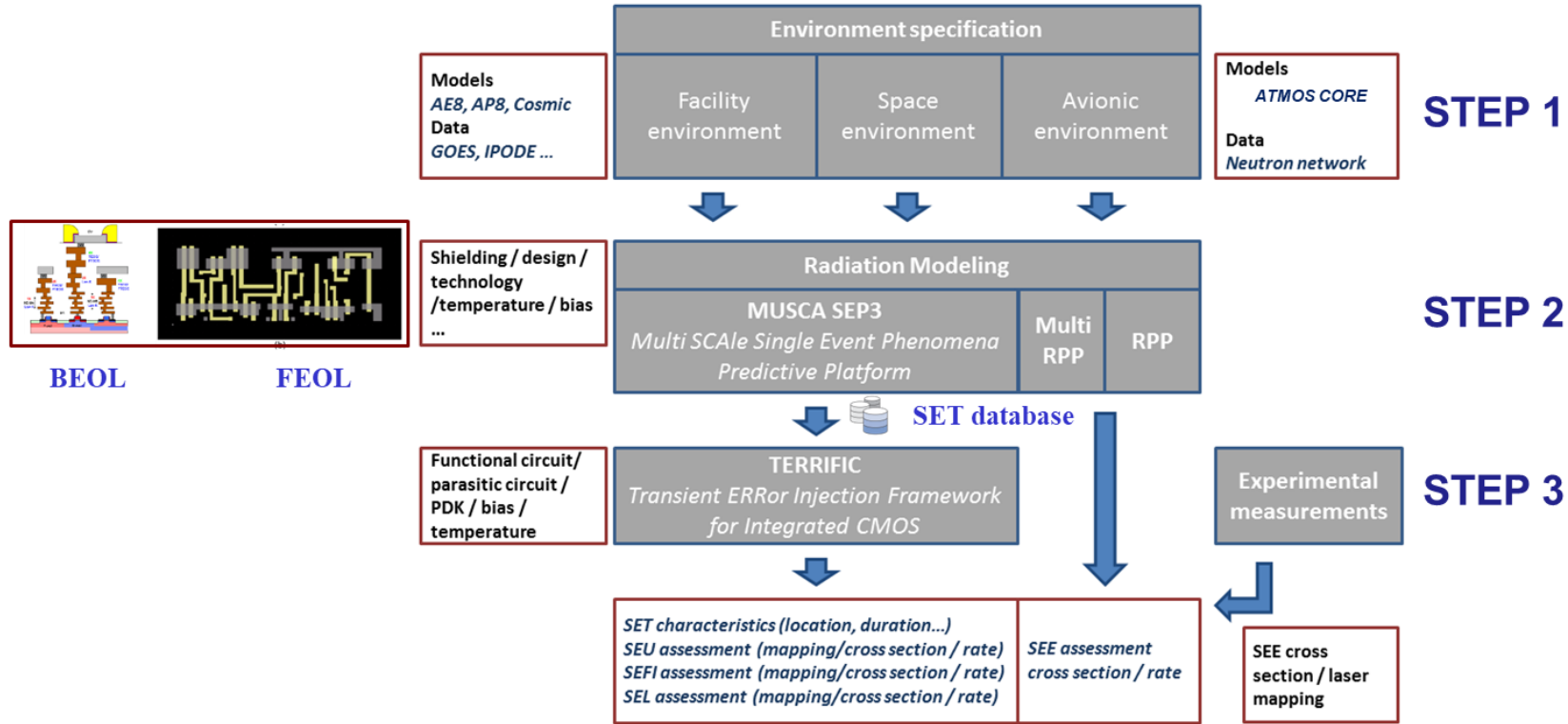
FinFET ... GAA



Advanced Approach

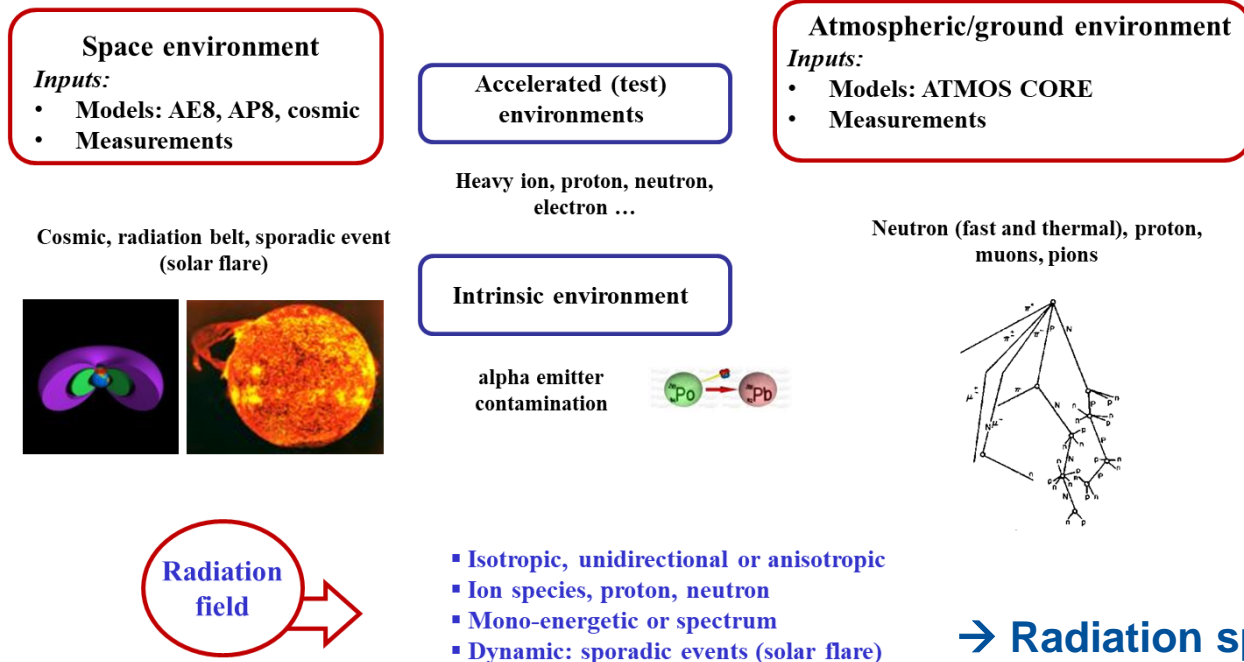


# Global framework of SEE modeling at ONERA



# STEP1: The radiation environment – MUSCA SEP3

## Definition of radiation constraints



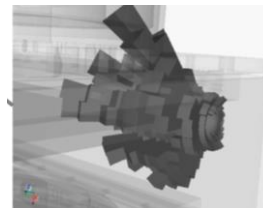
# STEP2: Radiation modeling – MUSCA SEP3 (1/2)

## ■ Definition of the local radiation environment

- Shielding definition (thickness and materials) in 3D
- Description of the Back-End-Of-Line (BEOL)

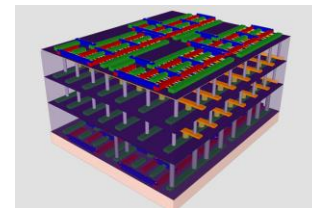
### Inputs:

Sector Shielding analysis

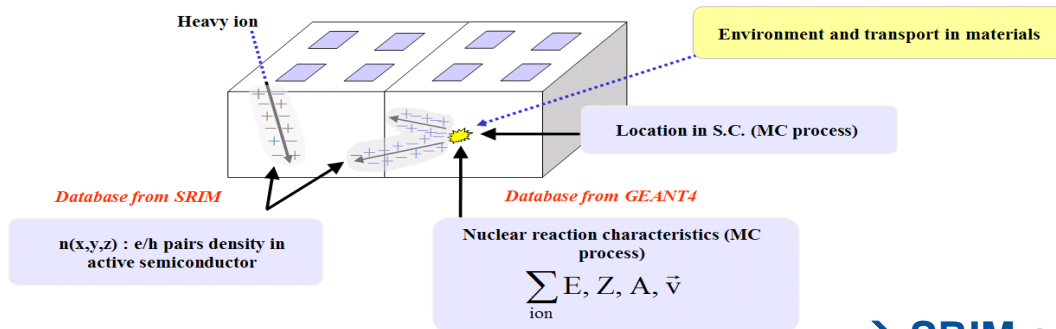


### Inputs:

IEDM roadmaps for BEOL  
PDK BEOL



## ■ Carrier generation in semiconductor



→ SRIM and/or GEANT database

# STEP2: Radiation modeling – MUSCA SEP3 (2/2)

- **Generation of SET database regarding the layout of gate/circuit**
  - 3D Analytical modeling of  $I(t)$
  - Modeling of each floating nodes

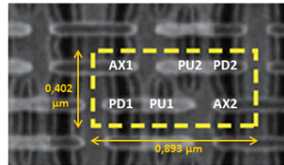
Design modeling:  
reverse engineering  
GDS extractor

Physical  
mechanisms

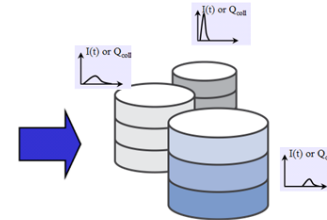
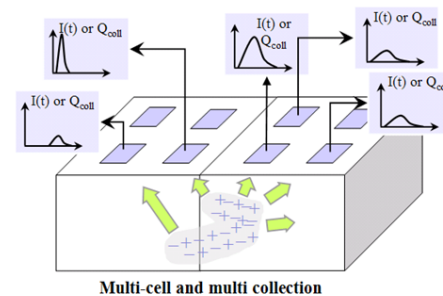
- Ambipolar and drift diffusions
- Potential/impedance variations
- Multi-collection and charge sharing
- Parasitic structure activation
- Bipolar amplification ...

SET database

**Inputs:**  
IEDM roadmap for FEOL  
GDS files  
PDK files



(b)



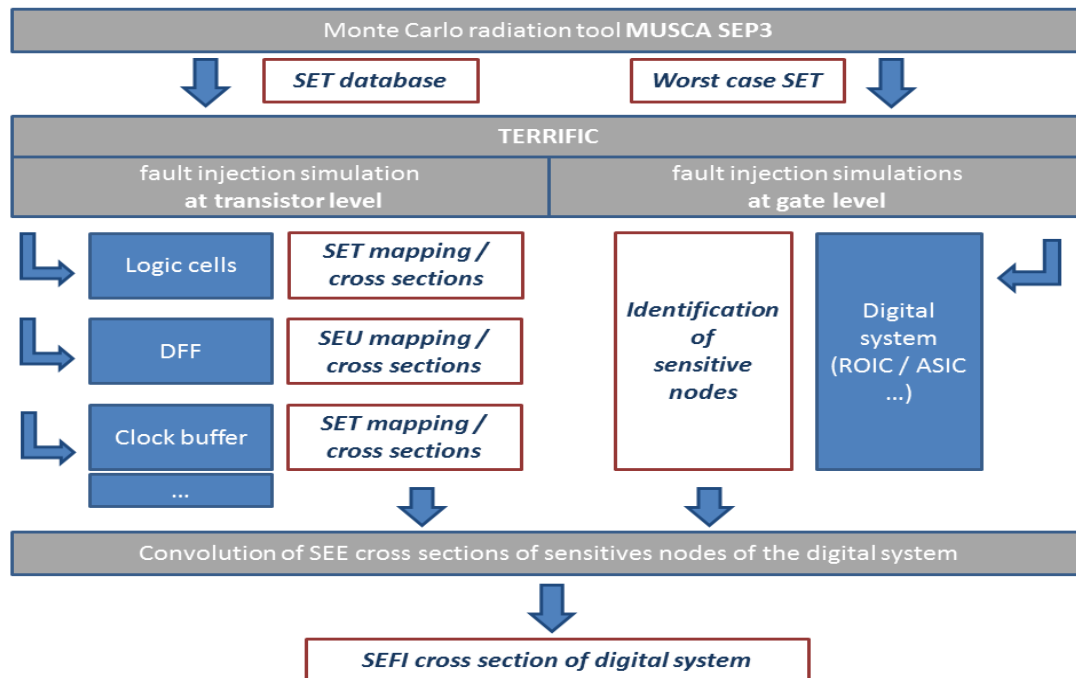
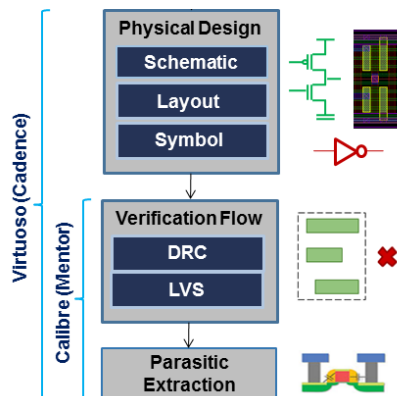
→ Fault injection at transistor and/or gate level

# STEP3: Fault injection – TERRIFIC

- Multiple fault injections and electrical simulations
  - SET/SEU/SEFI detection and post-process

## Inputs:

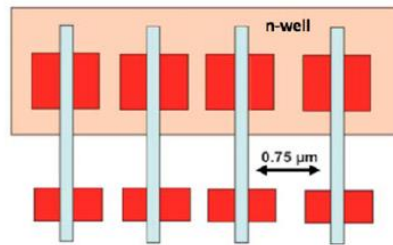
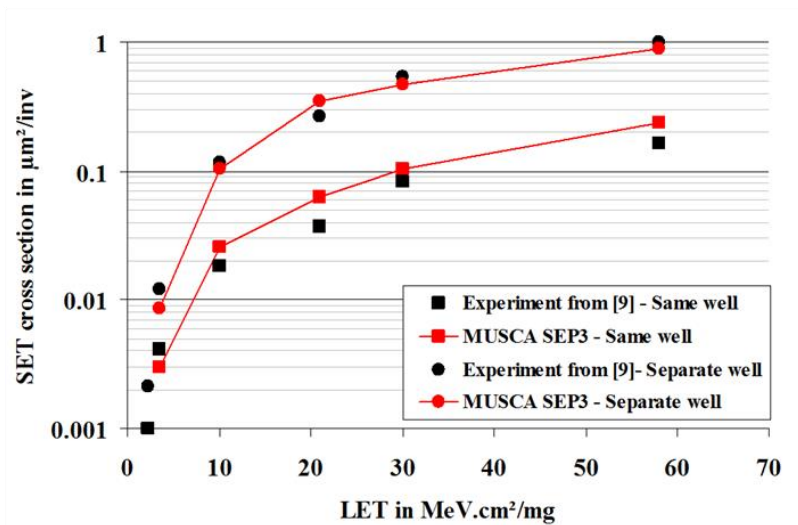
Gate/Circuit schematic  
PDK  
Inputs vectors / frequency ...



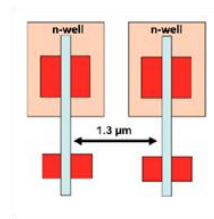


# Example of SEE modeling at ONERA

- **Pulse quenching in Bulk technologies**
  - Validation of SET cross section with SET measurements



Same Well



Separate Well

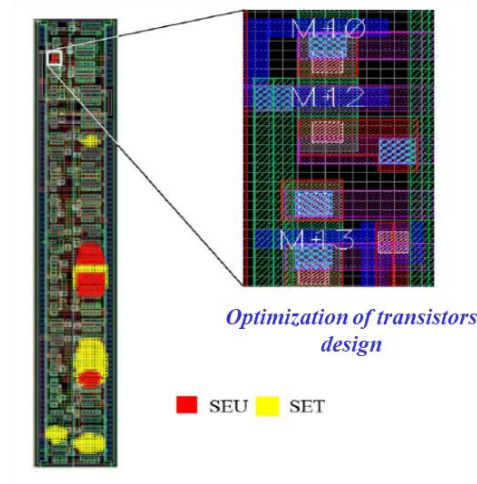
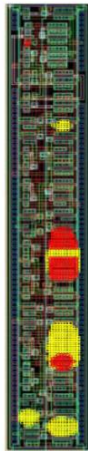
→ SET modeling with multi-collection and charge sharing allows for complex circuit feedback such as pulse quenching

# Example of SEE modeling at ONERA

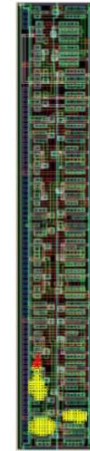
## ▪ Hardening by design

- Identify critical area and analyze failure occurrence at layout level → Support for design mitigation

*Original design*



*Optimized design*



→ Integration of MUSCA SEP3 in the MICROCHIP design flow since 2015

# Conclusions and perspectives

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- Since 2012 ONERA has developed a SEE prediction tool based on a multi-physics and multi-scale approach
  
- A global simulation framework for various activities
  - Study of emerging effects (multi-collection, techno/architecture dependence, particles)
  - Support for hardening by design digital gates and circuits
  - Support for *end user* analyses of COTS devices based on VLSI radiation database
  
- Technologies transfer to industries for addressing the space issues
  - For hardening radiation devices
  - Engineering tools derived from the ONERA methodology and models

## They trust in ONERA SEE modeling tools



*Thank you for your attention*

**Questions ?**

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